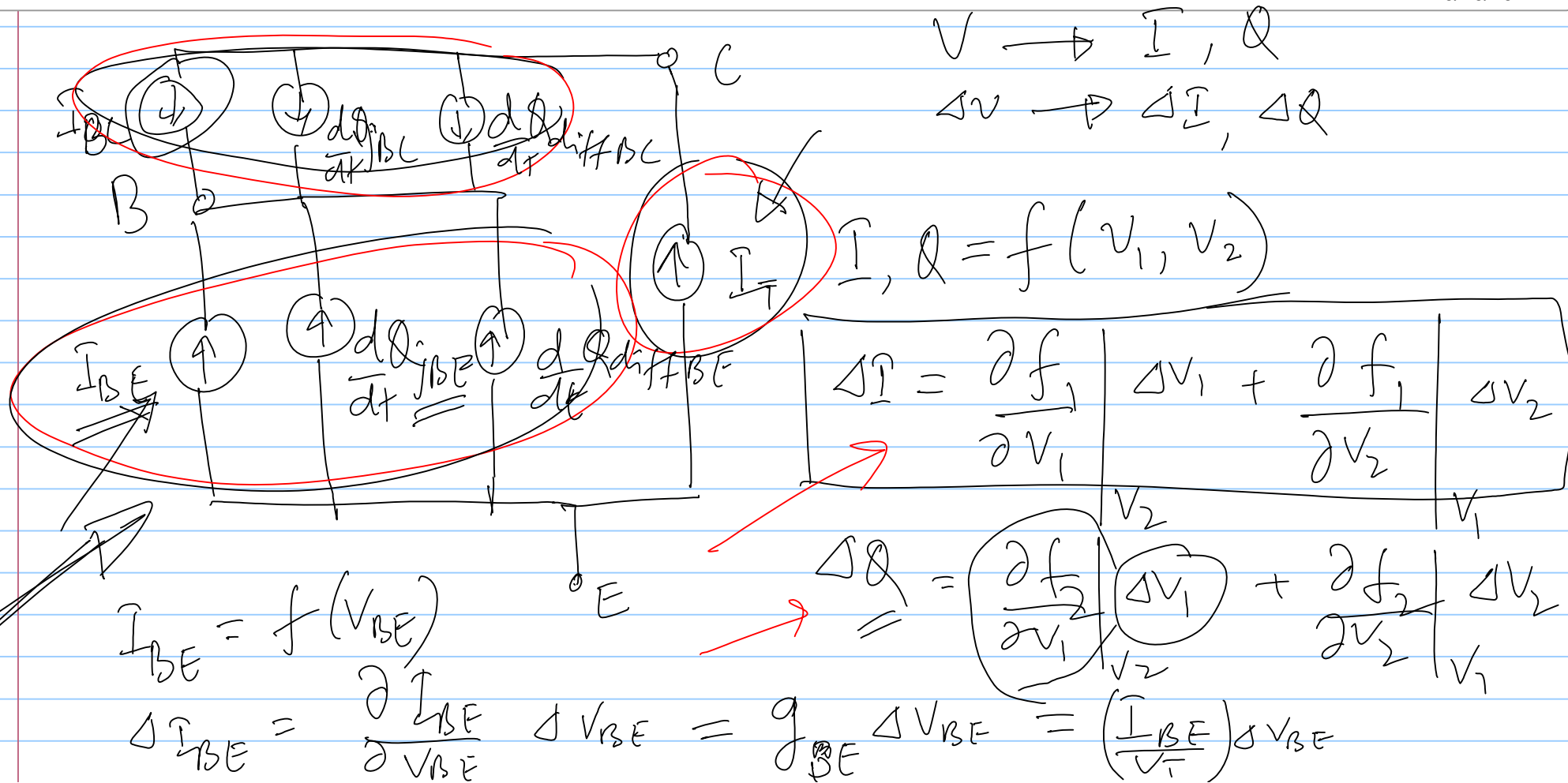
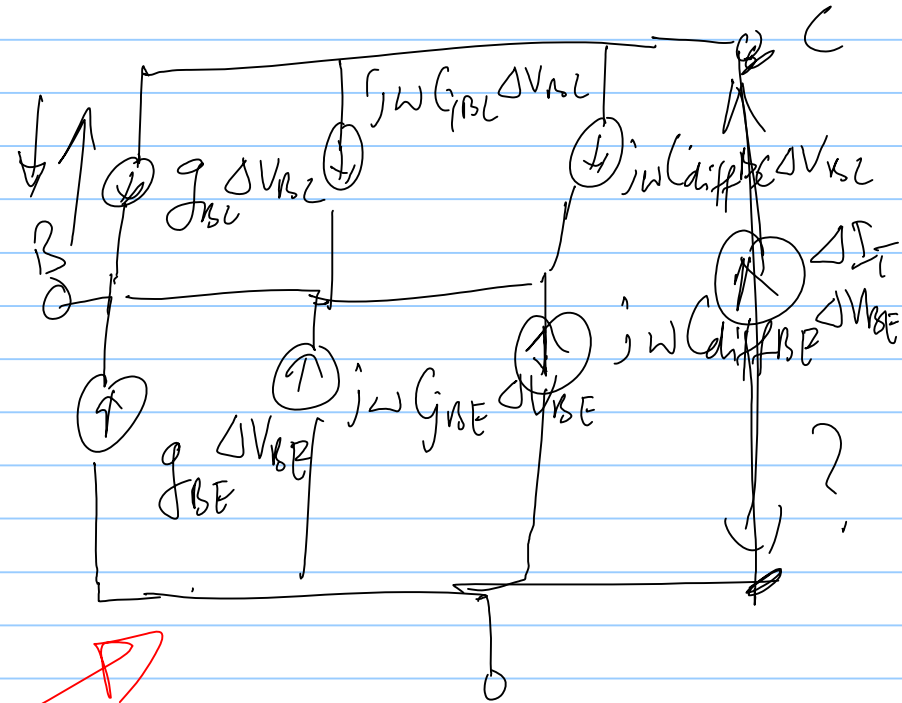
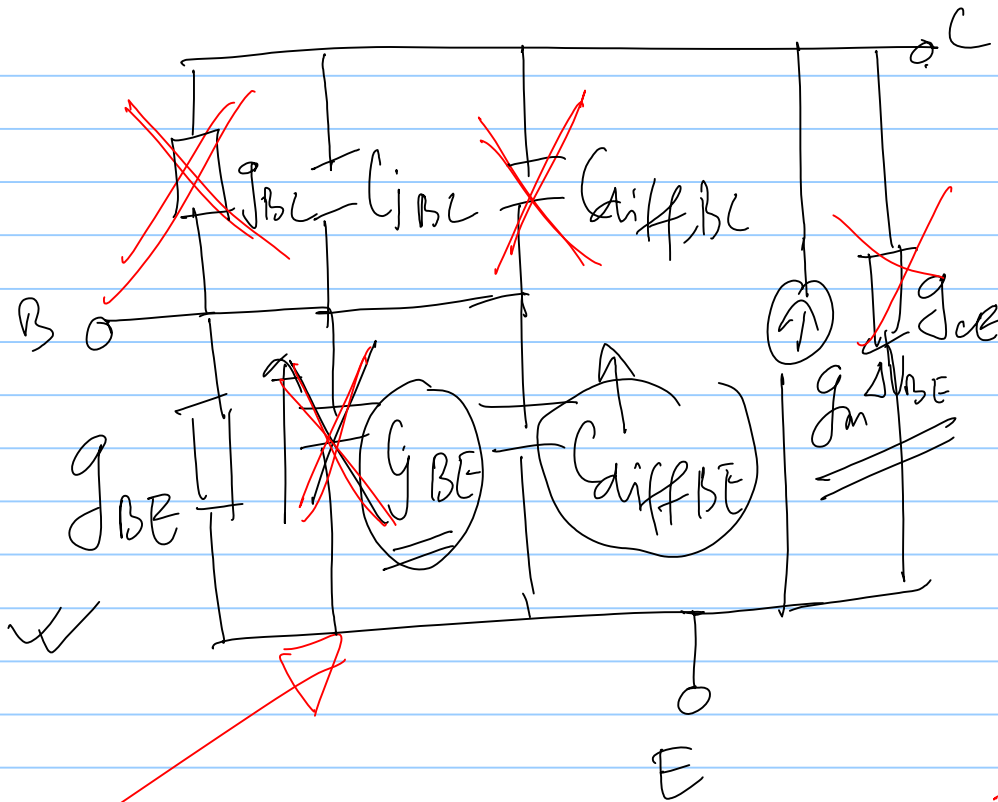


# Equivalent Circuit Model.

20/10/2014





$$\frac{dQ}{dt} \rightarrow j\omega \Delta Q = \underline{j\omega C \cdot \Delta V}$$

$$\underline{\partial I_T} = \frac{\partial I_T}{\partial V_{BE}} \Big|_{V_{BC}} \Delta V_{BE} + \frac{\partial I_T}{\partial V_{BC}} \Big|_{V_{BE}} \Delta V_{BC}$$

$$C_j(V) = \frac{\epsilon_{Si} A}{W(V)}$$

$$\int_0^V G_j dV = Q_j(V)$$

$$V_{BE} = V_{BC} + V_{CE}$$

$$= V_B - V_C + V_C - V_E$$

$$= V_{BE}$$

$$dV_{BC} = -dV_{CE} \text{ when } V_{BE} = \text{const}$$

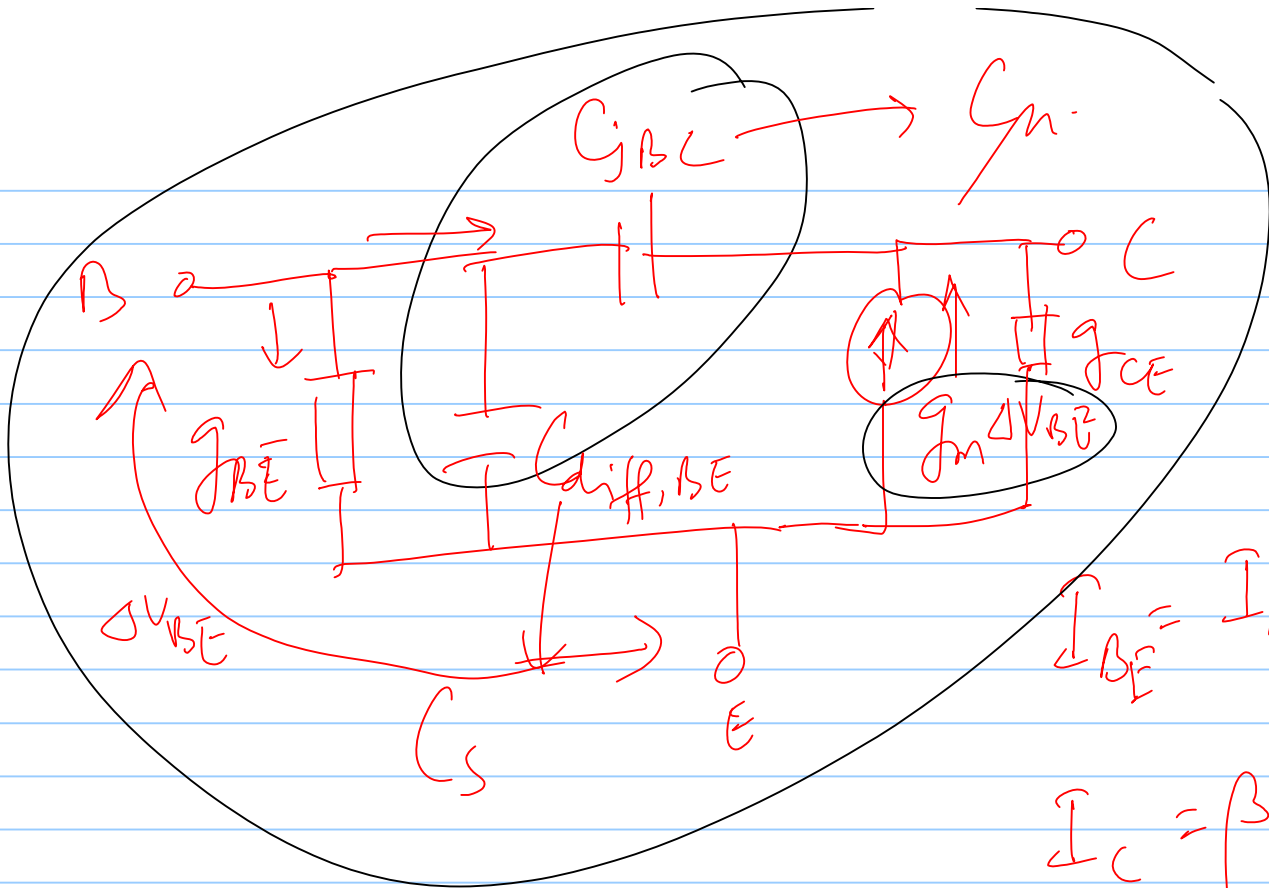
$$\left. \frac{\partial \hat{I}}{\partial V_{BC}} \right|_{V_{BE}}$$

$$\Delta V_{BC} =$$

$$\left. \frac{\partial \hat{I}}{\partial V_{CE}} \right|_{V_{BE}}$$

$$\Delta V_{CE}$$

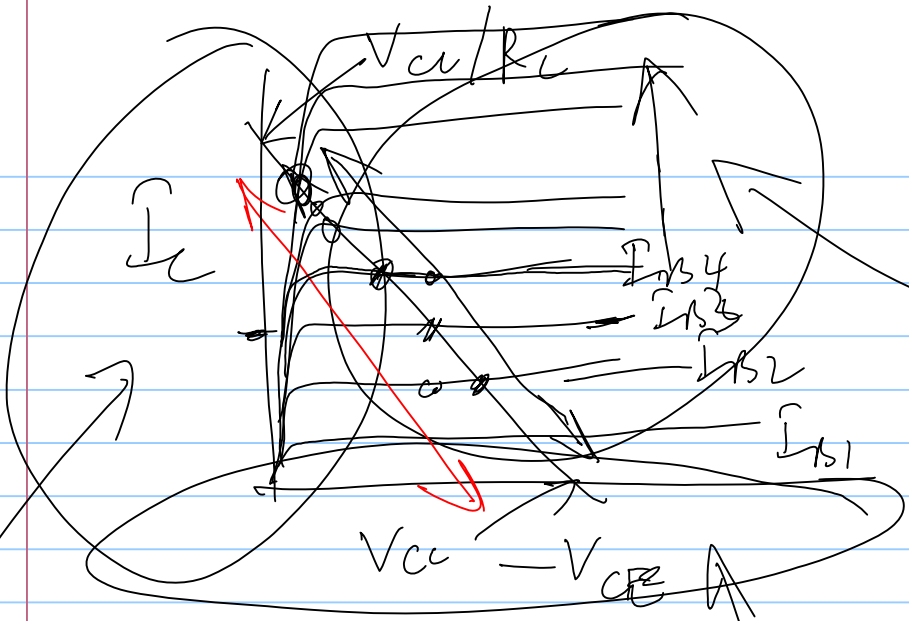
$$g_{CE}$$



$$I_{BE} = I_{BES} \left( e^{V_{BE}/V_T} - 1 \right)$$

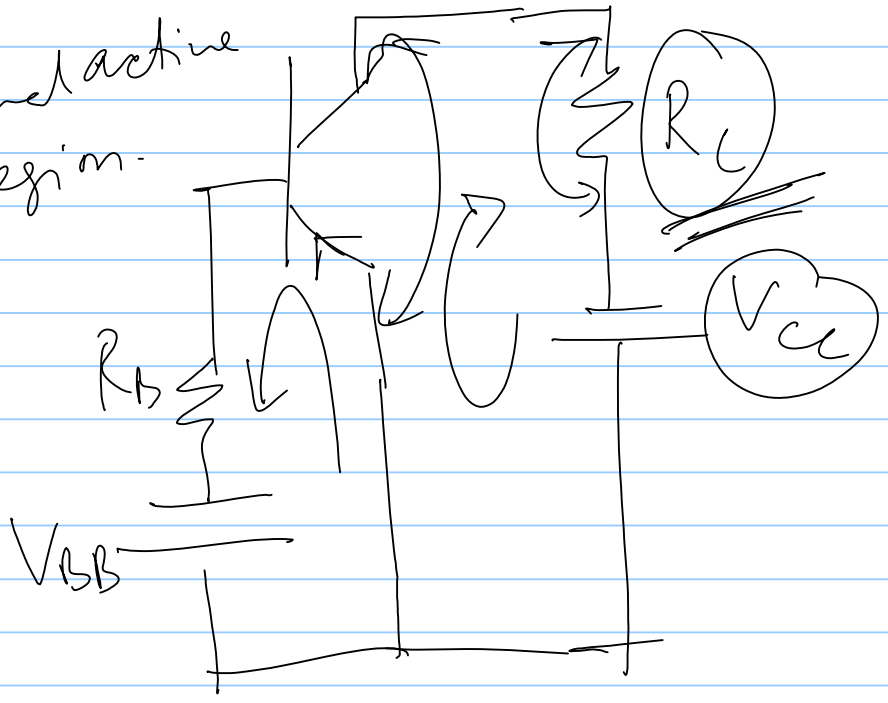
$$I_C = \beta I_{BE} = \beta I_{BES} \left( e^{V_{BE}/V_T} - 1 \right)$$

$$g_m = \frac{dI_C}{dV_{BE}} = \frac{I_C}{V_T}$$



Saturation p-n-p transistor region.

Normal active region.



Cutoff region 
$$V_{CC} = -V_{CE} + I_C R_C$$